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**Maximum ratings**

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	600	V
DC collector current, limited by $T_{vjmax}^{1)}$ $T_C = 25^\circ\text{C}$ value limited by bondwire $T_C = 100^\circ\text{C}$	$I_C$	140.0 120.0	A
Pulsed collector current, $t_p$ limited by $T_{vjmax}^{2)}$	$I_{Cpuls}$	300.0	A
Turn off safe operating area $V_{CE} \leq 600\text{V}$ , $T_{vj} \leq 175^\circ\text{C}^{3)}$	-	300.0	A
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Short circuit withstand time $V_{GE} = 15.0\text{V}$ , $V_{CC} \leq 400\text{V}$ Allowed number of short circuits < 1000 Time between short circuits: $\geq 1.0\text{s}$ $T_{vj} = 150^\circ\text{C}$	$t_{SC}$	5	$\mu\text{s}$
Power dissipation $T_C = 25^\circ\text{C}$	$P_{tot}$	714.0	W
Operating junction temperature	$T_{vj}$	-40...+175	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55...+150	$^\circ\text{C}$
Soldering temperature, wave soldering 1.6 mm (0.063 in.) from case for 10s		260	$^\circ\text{C}$
Mounting torque, M3 screw Maximum of mounting processes: 3	$M$	0.6	Nm

**Thermal Resistance**

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, <sup>4)</sup> junction - case	$R_{th(j-c)}$		0.21	K/W
Thermal resistance junction - ambient	$R_{th(j-a)}$		40	K/W

**Electrical Characteristic, at  $T_{vj} = 25^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0\text{V}$ , $I_C = 2.00\text{mA}$	600	-	-	V
Collector-emitter saturation voltage	$V_{CEsat}$	$V_{GE} = 15.0\text{V}$ , $I_C = 100.0\text{A}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 125^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	- - -	1.85 2.10 2.25	2.30 - -	V
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 1.60\text{mA}$ , $V_{CE} = V_{GE}$	4.1	5.1	5.7	V
Zero gate voltage collector current	$I_{CES}$	$V_{CE} = 600\text{V}$ , $V_{GE} = 0\text{V}$ $T_{vj} = 25^\circ\text{C}$ $T_{vj} = 175^\circ\text{C}$	- -	- -	40.0 6700.0	$\mu\text{A}$
Gate-emitter leakage current	$I_{GES}$	$V_{CE} = 0\text{V}$ , $V_{GE} = 20\text{V}$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE} = 20\text{V}$ , $I_C = 100.0\text{A}$	-	50.0	-	S

<sup>1)</sup> For maximal distance of 5mm between soldering point and mould

<sup>2)</sup> Additionally  $t_p < 10\text{ms}$  due to bondwire

<sup>3)</sup> Additionally  $t_p < 10\text{ms}$  due to bondwire

<sup>4)</sup> Thermal resistance of grease  $R_{th(c-s)}$  (case to heat sink) more than 0.1 K/W not included.